



EB13C3 H 2 H -27.000M

Series — RoHS Compliant (Pb-free) Low Current 3.3V 4 Pad 5mm x 7mm Ceramic SMD LVCMOS Oscillator

Frequency Tolerance/Stability — ±50ppm over -40°C to +85°C

Duty Cycle —— 50 ±5(%) Nominal Frequency 27.000MHz

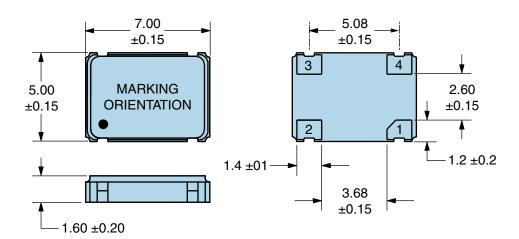
Logic Control / Additional Output Tri-State (High Impedance)

| ELECTRICAL SPECIFICATIONS | | |
|---------------------------------------|---|--|
| Nominal Frequency | 27.000MHz | |
| Frequency Tolerance/Stability | ±50ppm over -40°C to +85°C (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Ouput Load Change, First Year Aging at 25°C, Shock, and Vibration) | |
| Supply Voltage | 3.3Vdc ±10% | |
| Input Current | 5mA Maximum | |
| Output Voltage Logic High (Voh) | 90% of Vdd Minimum | |
| Input Current Logic High (Ioh) | -1.6mA | |
| Output Voltage Logic Low (Vol) | 10% of Vdd Maximum | |
| Input Current Logic Low (IoI) | +1.6mA | |
| Rise/Fall Time | 4nSec Maximum (Measured at 20% to 80% of waveform) | |
| Duty Cycle | 50 ±5(%) (Measured at 50% of waveform) | |
| Load Drive Capability | 15pF Maximum | |
| Output Logic Type | CMOS | |
| Logic Control / Additional Output | Tri-State (High Impedance) | |
| Tri-State Input Voltage (Vih and Vil) | 90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance) | |
| Standby Current | 10μA Maximum (Disabled Output: High Impedance) | |
| One Sigma Clock Period Jitter | 25pSec Maximum | |
| Start Up Time | 10mSec Maximum | |
| Storage Temperature Range | -55°C to +125°C | |

| ENVIRONMENTAL & MECHANICAL SPECIFICATIONS | | |
|---|---------------------------------------|--|
| Fine Leak Test | MIL-STD-883, Method 1014, Condition A | |
| Gross Leak Test | MIL-STD-883, Method 1014, Condition C | |
| Mechanical Shock | MIL-STD-202, Method 213, Condition C | |
| Resistance to Soldering Heat | MIL-STD-202, Method 210 | |
| Resistance to Solvents | MIL-STD-202, Method 215 | |
| Solderability | MIL-STD-883, Method 2003 | |
| Temperature Cycling | MIL-STD-883, Method 1010 | |
| Vibration | MIL-STD-883, Method 2007, Condition A | |



MECHANICAL DIMENSIONS (all dimensions in millimeters)



| PIN | CONNECTION |
|-----|----------------|
| 1 | Tri-State |
| 2 | Ground |
| 3 | Output |
| 4 | Supply Voltage |

| LINE | MARKING |
|------|---|
| 1 | ECLIPTEK |
| 2 | 27.000M |
| 3 | XXYZZ XX=Ecliptek Manufacturing Code Y=Last Digit of the Year ZZ=Week of the Year |

Suggested Solder Pad Layout

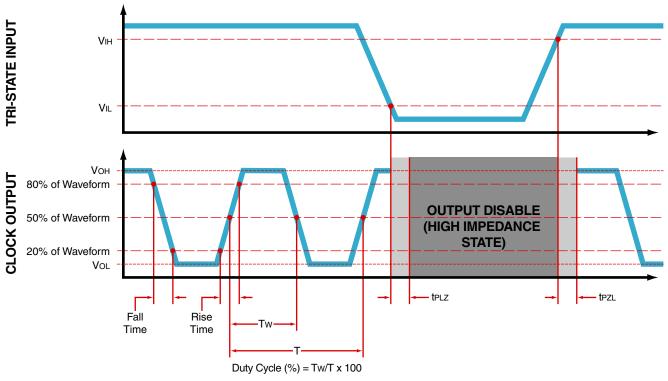
All Dimensions in Millimeters



All Tolerances are ±0.1



OUTPUT WAVEFORM & TIMING DIAGRAM



Test Circuit for CMOS Output



- Note 1: An external $0.1\mu F$ low frequency tantalum bypass capacitor in parallel with a $0.01\mu F$ high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.
- Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.
- Note 3: Capacitance value \dot{C}_L includes sum of all probe and fixture capacitance.



Recommended Solder Reflow Methods



High Temperature Infrared/Convection

| T _s MAX to T _∟ (Ramp-up Rate) | 3°C/second Maximum |
|---|---|
| Preheat | |
| - Temperature Minimum (T _s MIN) | 150°C |
| - Temperature Typical (T _s TYP) | 175°C |
| - Temperature Maximum (T _s MAX) | 200°C |
| - Time (t _s MIN) | 60 - 180 Seconds |
| Ramp-up Rate (T _L to T _P) | 3°C/second Maximum |
| Time Maintained Above: | |
| - Temperature (T _L) | 217°C |
| - Time (t∟) | 60 - 150 Seconds |
| Peak Temperature (T _P) | 260°C Maximum for 10 Seconds Maximum |
| Target Peak Temperature (T _P Target) | 250°C +0/-5°C |
| Time within 5°C of actual peak (tp) | 20 - 40 seconds |
| Ramp-down Rate | 6°C/second Maximum |
| Time 25°C to Peak Temperature (t) | 8 minutes Maximum |
| Moisture Sensitivity Level | Level 1 |
| Additional Notes | Temperatures shown are applied to body of device. |



Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 240°C

| T _s MAX to T _L (Ramp-up Rate) | 5°C/second Maximum |
|---|--|
| Preheat | |
| - Temperature Minimum (T _s MIN) | N/A |
| - Temperature Typical (T _s TYP) | 150°C |
| - Temperature Maximum (T _s MAX) | N/A |
| - Time (t _s MIN) | 60 - 120 Seconds |
| Ramp-up Rate (T _L to T _P) | 5°C/second Maximum |
| Time Maintained Above: | |
| - Temperature (T _L) | 150°C |
| - Time (t∟) | 200 Seconds Maximum |
| Peak Temperature (T _P) | 240°C Maximum |
| Target Peak Temperature (T _P Target) | 240°C Maximum 1 Time / 230°C Maximum 2 Times |
| Time within 5°C of actual peak (tp) | 10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time |
| Ramp-down Rate | 5°C/second Maximum |
| Time 25°C to Peak Temperature (t) | N/A |
| Moisture Sensitivity Level | Level 1 |
| Additional Notes | Temperatures shown are applied to body of device. |

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)